Jongwon Lee

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Implementation of Flip-Chip Microbump Bonding between InP and SiC Substrates for Millimeter-Wave Applications. Micromachines, 2022, 13, 1072.	2.9	1
2	692 GHz High-Efficiency Compact-Size InP-Based Fundamental RTD Oscillator. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 716-719.	3.1	7
3	Sidewall Slope Control of InP Via Holes for 3D Integration. Micromachines, 2021, 12, 89.	2.9	1
4	Area-Efficient Series-Connected Resonant Tunneling Diode Pair as Binary Neuron in Cellular Neural Network. IEEE Electron Device Letters, 2020, 41, 1308-1311.	3.9	2
5	225â€GHz tripleâ€push RTD oscillator with 0.5â€mW dcâ€power consumption. IET Circuits, Devices and Systems, 2020, 14, 209-215.	1.4	1
6	Noise analysis of reflectionâ€ŧype microwave RTD amplifier. IET Circuits, Devices and Systems, 2020, 14, 966-971.	1.4	0
7	RF Power Analysis on 5.8 GHz Low-Power Amplifier Using Resonant Tunneling Diodes. IEEE Microwave and Wireless Components Letters, 2017, 27, 61-63.	3.2	9
8	Characterization of a selfâ€aligned RTD using a SiNx sidewall process for highâ€speed applications. Microwave and Optical Technology Letters, 2017, 59, 3073-3076.	1.4	0
9	A 675 GHz Differential Oscillator Based on a Resonant Tunneling Diode. IEEE Transactions on Terahertz Science and Technology, 2016, 6, 510-512.	3.1	14
10	A sub-mW D-band 2 nd harmonic oscillator using InP-based quantum-effect tunneling devices. , 2014, , .		0
11	Reflection-Type RTD Low-Power Amplifier With Deep Sub-mW DC Power Consumption. IEEE Microwave and Wireless Components Letters, 2014, 24, 551-553.	3.2	15
12	Negative-differential-conductance RTD amplifier MMIC with record foms of gain-to-dc power ratio and noise figure. , 2014, , .		0
13	5 GHz low-power RTD-based amplifier MMIC with a high figure-of-merit of 24.5 dB/mW. , 2013, , .		4
14	A 1.3 pJ/bit energy-efficient ultra-low power on-off mode oscillator using an InP-based quantum-effect tunneling device. , 2012, , .		0
15	An On–Off Mode RTD Oscillator Operating at Extremely Low Power Consumption. IEEE Nanotechnology Magazine, 2012, 11, 863-865.	2.0	17
16	A Low-Power 40-Gb/s 1:2 Demultiplexer IC Based on a Resonant Tunneling Diode. IEEE Nanotechnology Magazine, 2012, 11, 431-434.	2.0	9
17	40 Gb/s Low-Power 4:1 Multiplexer Based on Resonant Tunneling Diodes. IEEE Nanotechnology Magazine, 2012, 11, 890-895.	2.0	8
18	Implementation of a 4∶1 multiplexing quantum-effect IC based on RTD circuit topology. , 2010, , .		3

Implementation of a 4∶1 multiplexing quantum-effect IC based on RTD circuit topology. , 2010, , . 18

#	Article	IF	CITATIONS
19	A Novel High-Speed Multiplexing IC Based on Resonant Tunneling Diodes. IEEE Nanotechnology Magazine, 2009, 8, 482-486.	2.0	25
20	A Low DC-Power Multiplexer IC using an InP-based CML-MOBILE RTD/HBT Technology. , 2008, , .		4
21	Implementation of a New Functional Digital IC for Multiplexing Operation Based on RTDs. , 2008, , .		Ο